

TECHNICAL DATA
DATA SHEET 4788, REV. C**SILICON SCHOTTKY RECTIFIER**
Low Reverse Leakage
150°C Operating Temperature**Applications:**

- Switching Power Supply
- Converters
- Free-Wheeling Diodes
- Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

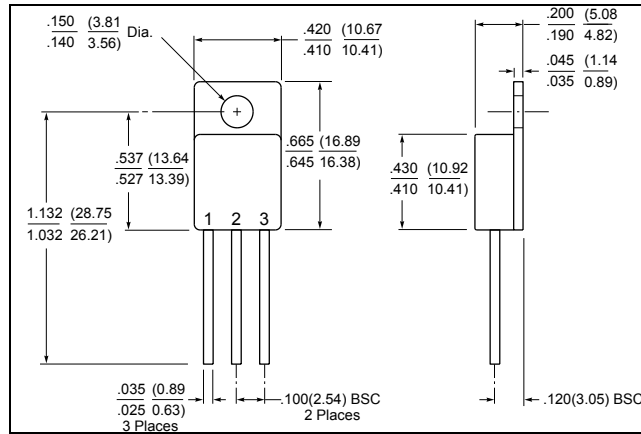
Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	16	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave	75	A
Max. Junction Temperature	T_J	-	-65 to +150	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C
Thermal Resistance	$R_{\theta JC}$	Per diode	1.5	°C/W

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 16A, Pulse, $T_J = 25\text{ °C}$	0.90	V
	V_{F2}	@ 16A, Pulse, $T_J = 125\text{ °C}$	0.71	V
Max. Reverse Current	I_{R1}	@ $V_R = 100V$, Pulse, $T_J = 25\text{ °C}$	0.75	mA
	I_{R2}	@ $V_R = 100V$, Pulse, $T_J = 125\text{ °C}$	15	mA
Max. Junction Capacitance	C_T	@ $V_R = 5V$, $T_C = 25\text{ °C}$ $f_{SIG} = 1MHz$, $V_{SIG} = 50mV$ (p-p)	1000	pF

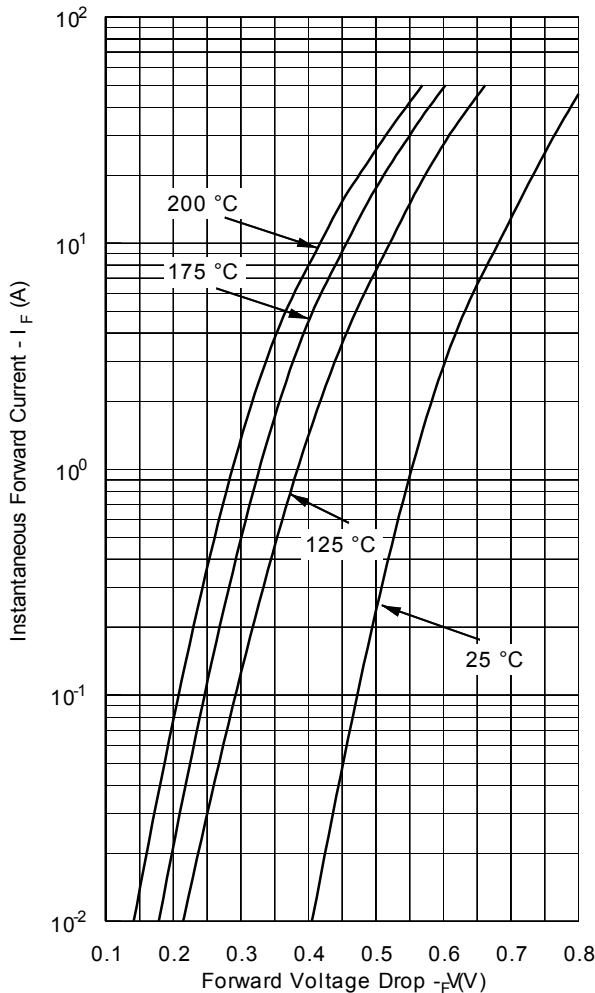
Mechanical Dimensions: In Inches / mm



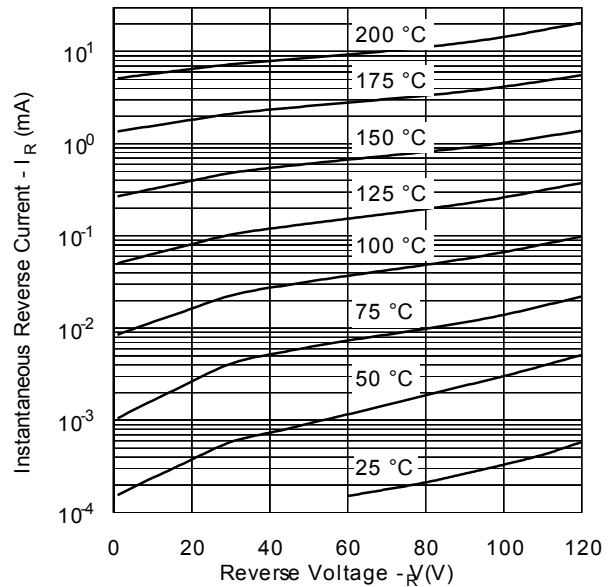
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DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

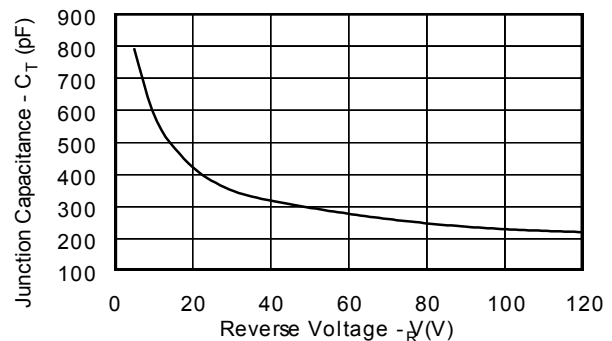
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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